SSC8L3622GN4

Dual N-Channel Enhancement MOSFET

➢ Features

V_{DS}	V_{GS}	$R_{DS(ON)}$ Typ.	I_D
60V	±20V	12.5mΩ@10V	32A
		16mΩ@4.5V	

➢ Description

The SSC8L3622GN4 is N-Channel enhancement mode MOSFET. Uses SGT Technology and design to provide excellent RDSON with low gate charge. This device is suitable for use in DC - DC conversion, power switch and charging circuit.

100% UIS + ΔVDS + Rg Tested!

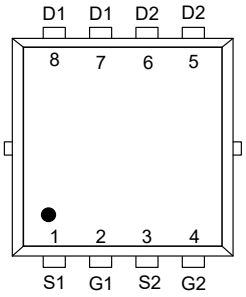
➢ Applications

- Inverter
- DC-DC Converter
- Half and Full Bridge Topology
- Motor Drive Control

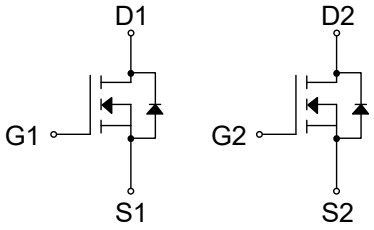
➢ Ordering Information

Device	Package	Shipping
SSC8L3622GN4	PDFN3.3X3.3-8L	5000/Reel

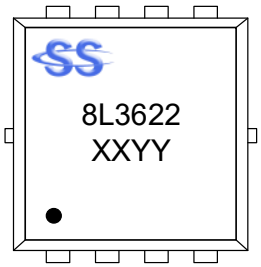
➢ Pin configuration



PDFN3.3x3.3-8L (Top View)



Pin Configuration



Marking

(XXYY: Internal Traceability Code)

➢ Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter		Ratings	Unit
V_{DSS}	Drain-to-Source Voltage		60	V
V_{GSS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current [b]	T_C = 25℃	32	A
		T_C = 100℃	18	A
I_{DM}	Pulsed Drain Current [b]		120	A
I_{DSM}	Continuous Drain Current [a]	T_A = 25℃	10	A
		T_A = 70℃	7	A
P_D	Power Dissipation [c]	T_C = 25℃	21	W
		T_C = 100℃	8.6	W
P_{DSM}	Power Dissipation [a]	T_A = 25℃	2.3	W
		T_A = 70℃	1.45	W
I_{AS}	Avalanche Current [b] L = 0.5mH		15	A
E_{AS}	Avalanche Energy [b] L = 0.5mH		56.25	mJ
T_J	Operation junction temperature		-55 to 150	℃
T_{STG}	Storage temperature range		-55 to 150	℃

➢ Thermal Resistance Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance [a]	55	℃/W
$R_{\theta JC}$	Junction-to-Case Thermal Resistance	5.8	

Note:

a. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz.copper,in a still air environment with T_A=25℃.The value in any given application depends on the user is specific board design. The current rating is based on the t≤10s thermal resistance rating.

b. Repetitive rating, pulse width limited by junction temperature.

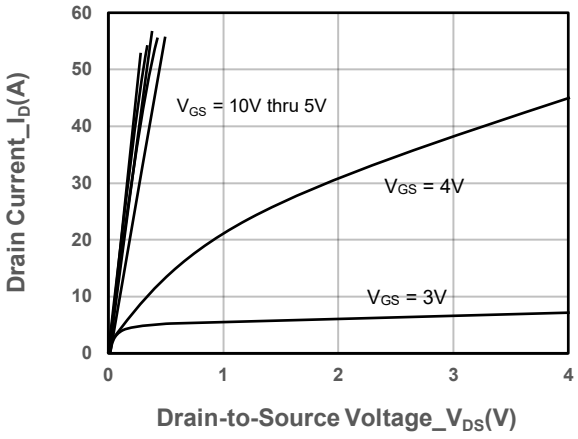
c. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

d. The maximum current rating is package limited.

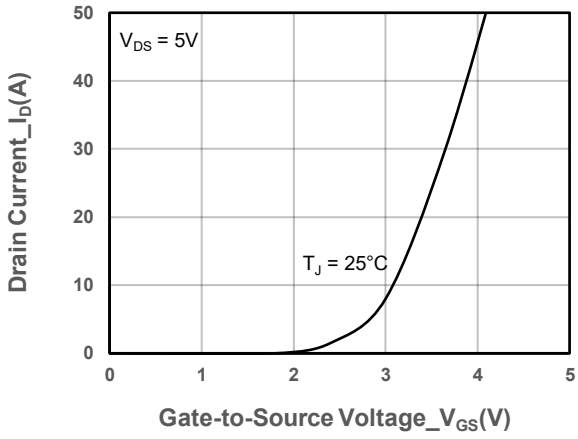
➢ Electrical Characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250uA	1	1.7	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 15A		12.5	17	mΩ
		V_{GS} = 4.5V, I_D = 10A		16	21	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60V, V_{GS} = 0V			1	μA
Gate-Source Leak Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
Forward Voltage	V_{SD}	V_{GS} = 0V, I_S = 1A		0.7	1.2	V
Gate Resistance	R_G	V_{DS} = 0V, f = 1MHz		1.3		Ω
Input Capacitance	C_{ISS}	V_{DS} = 30V, V_{GS} = 0V, f = 1MHz		600		pF
Output Capacitance	C_{OSS}			205		
Reverse Transfer Capacitance	C_{RSS}			8		
Total Gate Charge	Q_G	V_{GS} = 10V, V_{DS} = 30V, I_D = 15A		9.6		nC
Gate to Source Charge	Q_{GS}			1.9		
Gate to Drain Charge	Q_{GD}			1.3		
Turn-on Delay Time	$T_{D(ON)}$	V_{GS} = 10V, V_{DS} = 30V, I_D = 15A, R_G = 3Ω		3.5		ns
Rise Time	T_r			10.8		
Turn-off Delay Time	$T_{D(OFF)}$			9.6		
Fall Time	T_f			4.3		
Diode Recovery Time	T_{rr}	I_F=20A, di/dt=100A/us		23		ns
Diode Recovery Charge	Q_{rr}	I_F=20A, di/dt=100A/us		13.5		nC

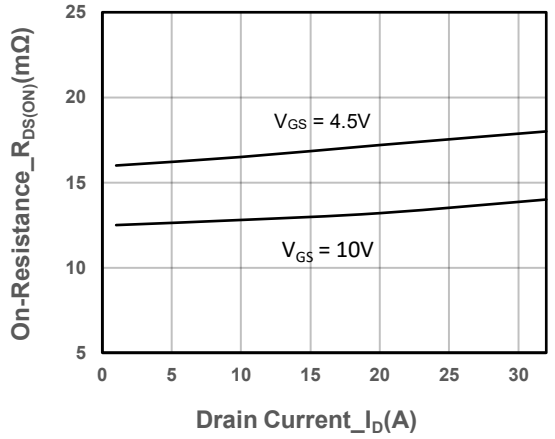
➢ Typical Performance Characteristics (T_A=25℃ unless otherwise noted)



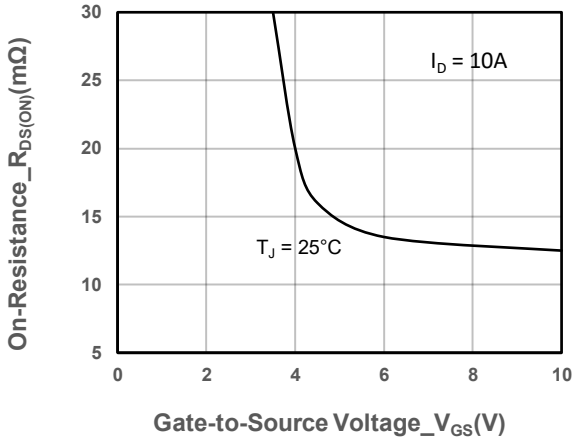
Output Characteristics



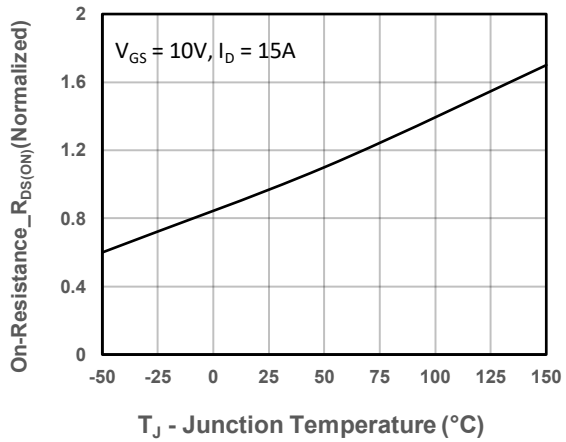
Transfer Characteristics



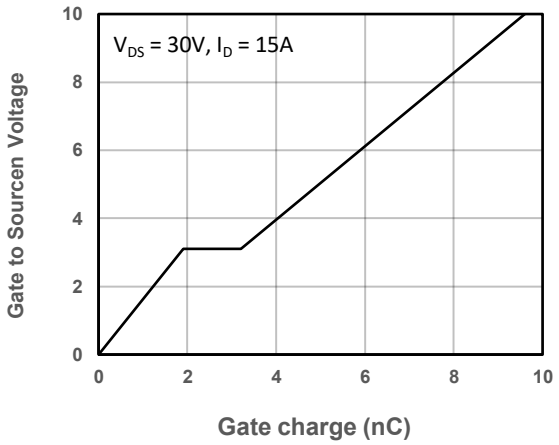
On-Resistance vs. Drain Current and Gate Voltage



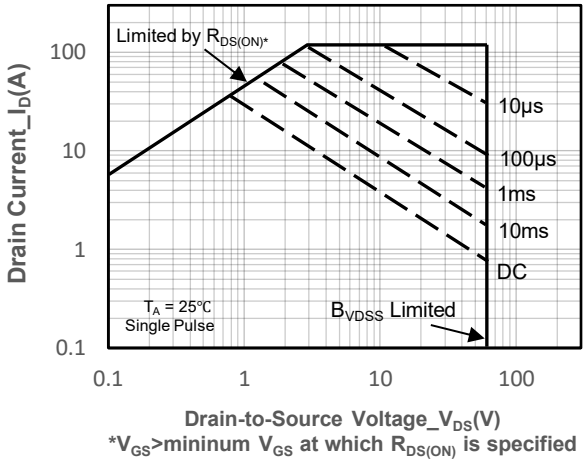
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature

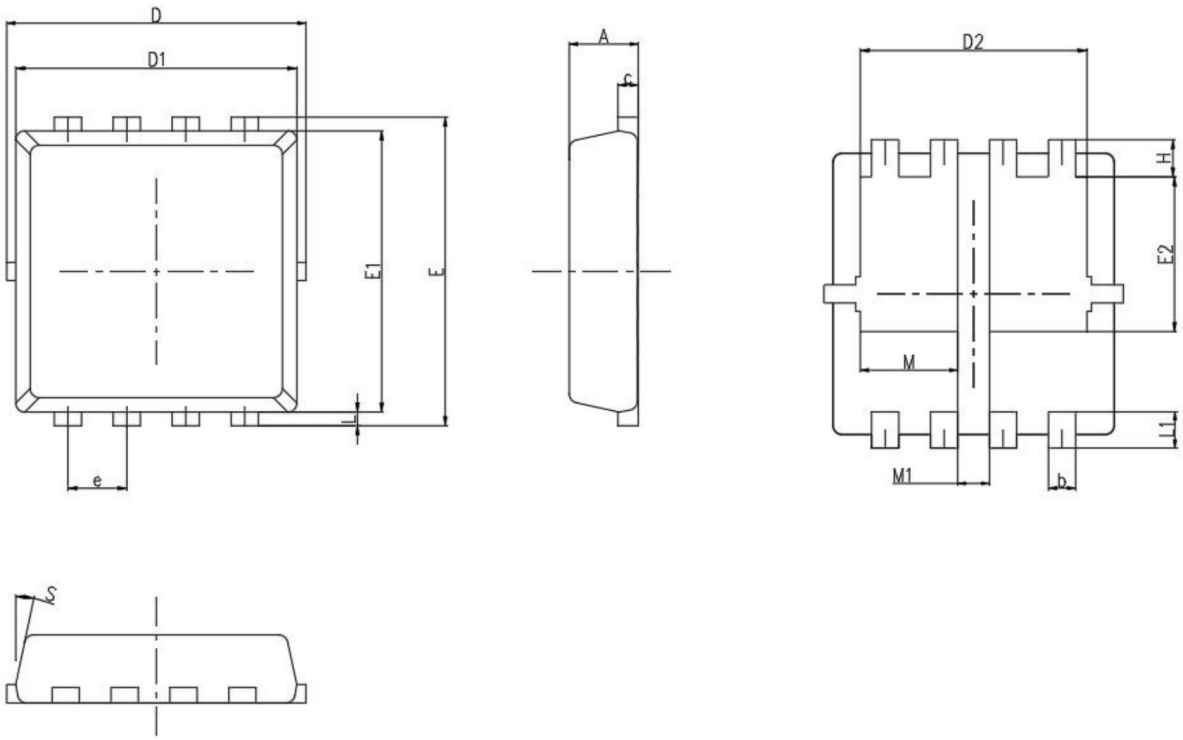


Gate-Source Voltage vs. Gate charge



Safe Operating Area vs. Junction-to-Ambient

➢ Package Information



Symbol	MILL IMETER		
	Min	Nom	Max
A	0.60	0.75	0.90
b	0.25	0.30	0.35
c	0.10	0.20	0.30
D	3.00	3.20	3.45
D1	3.05	3.15	3.25
D2	2.40	2.50	2.60
E	3.10	3.30	3.50
E1	2.90	3.05	3.20
E2	1.55	1.75	1.95
e	0.65BSC		
H	0.20	0.40	0.57
L	0.06	0.10	0.20
L1	0.30	0.40	0.55
S	10°	12°	14°
M	0.95	1.05	1.15
M1	0.4BSC		

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